

## NPN Transistors

### 2SC4984

#### ■ Features

- Collector Current Capability  $I_C=1.5A$
- Collector Emitter Voltage  $V_{CE0}=15V$
- Complementary to 2SA1882

#### ■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CBO}$	15	V
Collector - Emitter Voltage	$V_{CEO}$	15	
Emitter - Base Voltage	$V_{EBO}$	5	
Collector Current - Continuous	$I_C$	1.5	A
Collector Current - Pulse	$I_{CP}$	3	
Base Current	$I_B$	0.3	
Collector Power Dissipation (Note.1)	$P_C$	1.3	W
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55 to 150	

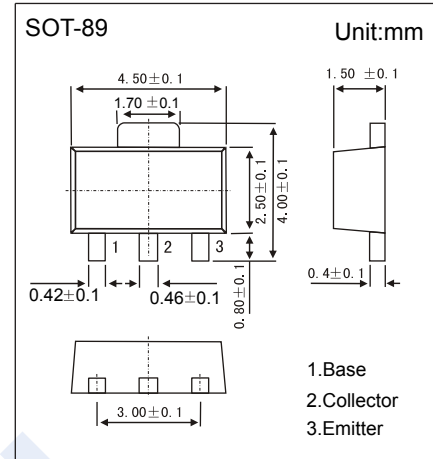
Note.1 : Mounted on ceramic substrate of  $250mm^2 \times 0.8mm$

#### ■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CBO}$	$I_C = 100 \mu A, I_E = 0$	15			V
Collector- emitter breakdown voltage	$V_{CEO}$	$I_C = 1 mA, R_{BE} = \infty$	15			
Emitter - base breakdown voltage	$V_{EBO}$	$I_E = 100 \mu A, I_C = 0$	5			
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = 12 V, I_E = 0$			0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 4 V, I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 5mA, I_B = 0.5mA$			25	mV
		$I_C = 500mA, I_B = 25mA$			240	
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500mA, I_B = 25mA$			1.2	V
DC current gain	$h_{FE}$	$V_{CE} = 2V, I_C = 50mA$	140		560	
		$V_{CE} = 2V, I_C = 1 A$	70			
Collector output capacitance	$C_{ob}$	$V_{CB} = 10V, f = 1MHz$		10		pF
Transition frequency	$f_T$	$V_{CE} = 2V, I_C = 50mA$		200		MHz

#### ■ Classification of $h_{fe}(1)$

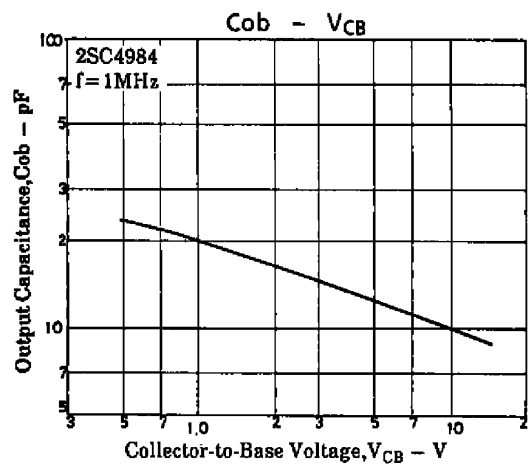
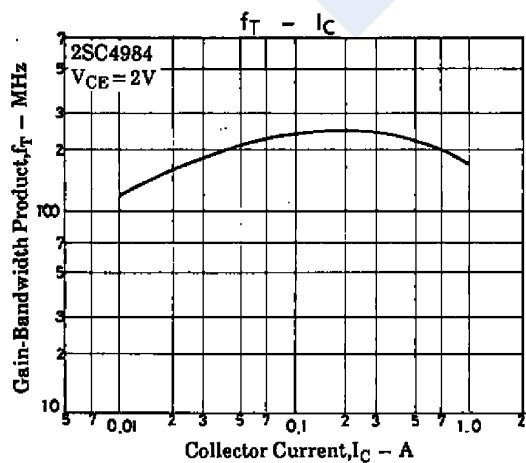
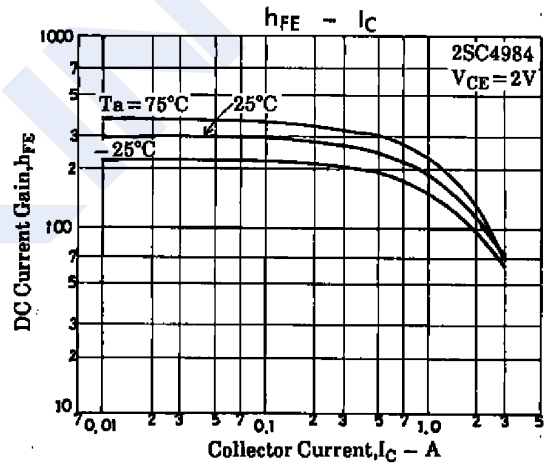
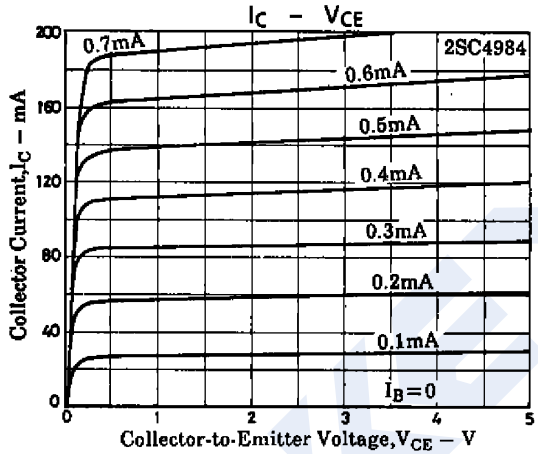
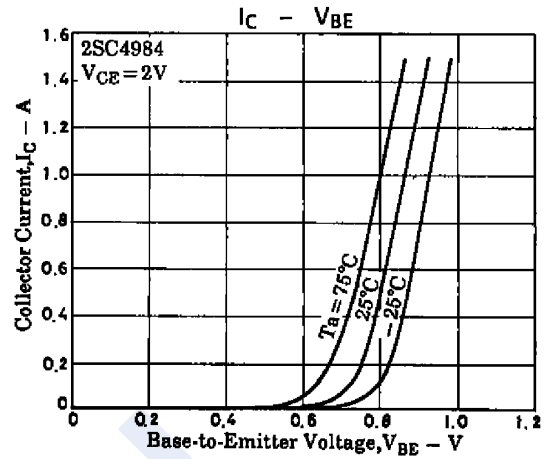
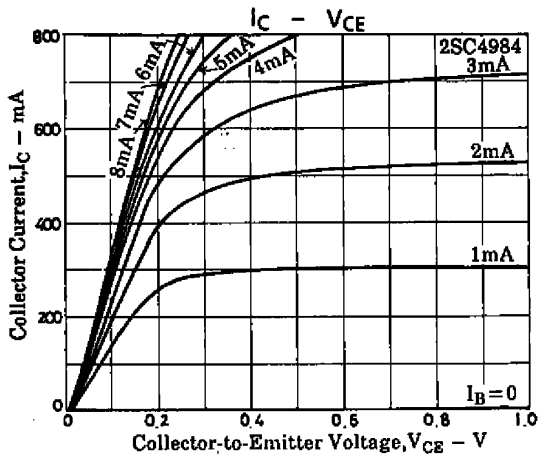
Type	2SC4984-S	2SC4984-T	2SC4984-U
Range	140-280	200-400	280-560
Marking	CT S*	CT T*	CT U*



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■ Typical Characteristics



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